

ABSTRACT OF THE DISCLOSURE

A semiconductor integrated circuit device has a MOS transistor M2 including a parasitic diode Dx2 for preventing a reverse current due to a parasitic diode Dx1 of a MOS transistor M1. The semiconductor integrated circuit device further has a voltage setting circuit 1 for turning the MOS transistor M2 off in a reversely biased state, and an anti-reverse-current element 2 for preventing a reverse current from flowing through the voltage setting circuit 1 in a reversely biased state. In normal operation, a direct-current voltage within the withstand voltage range of the MOS transistor M2 is fed to the gate thereof according to the voltage applied to the conductive terminal 6y of the MOS transistor M2.